## **High Voltage Transistors**

## **NPN Silicon**

#### **Features**

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>CEO</sub>	300 200	Vdc
Collector - Base Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>CBO</sub>	300 200	Vdc
Emitter – Base Voltage MMBTA42, SMMBTA42 MMBTA43	V <sub>EBO</sub>	6.0 6.0	Vdc
Collector Current - Continuous	Ic	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

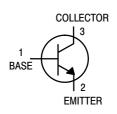
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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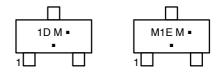
http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6

#### **MARKING DIAGRAMS**



1D = MMBTA42LT, SMMBTA42L

M1E = MMBTA43LT M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•	•	•
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBTA42, SMMBTA42 MMBTA43	V <sub>(BR)CEO</sub>	300 200	_ _	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	MMBTA42, SMMBTA42 MMBTA43	V <sub>(BR)CBO</sub>	300 200	- -	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 100 \mu Adc, I_C = 0$ )		V <sub>(BR)EBO</sub>	6.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 200 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 160 \text{ Vdc}, I_E = 0)$	MMBTA42, SMMBTA42 MMBTA43	Ісво	- -	0.1 0.1	μAdc
Emitter Cutoff Current $ \begin{aligned} &(\text{V}_{\text{EB}} = 6.0 \text{ Vdc, I}_{\text{C}} = 0) \\ &(\text{V}_{\text{EB}} = 4.0 \text{ Vdc, I}_{\text{C}} = 0) \end{aligned} $	MMBTA42, SMMBTA42 MMBTA43	I <sub>EBO</sub>	- -	0.1 0.1	μAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	Both Types Both Types	h <sub>FE</sub>	25 40	- -	-
( $I_C = 30 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	MMBTA42, SMMBTA42 MMBTA43		40 40	- -	
Collector – Emitter Saturation Voltage ( $I_C = 20 \text{ mAdc}$ , $I_B = 2.0 \text{ mAdc}$ )	MMBTA42, SMMBTA42 MMBTA43	V <sub>CE(sat)</sub>	_ _	0.5 0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = 20 \text{ mAdc}$ , $I_B = 2.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	-	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS			•	•	•
Current – Gain – Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)		f <sub>T</sub>	50	_	MHz
Collector-Base Capacitance (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	MMBTA42, SMMBTA42 MMBTA43	C <sub>cb</sub>	- -	3.0 4.0	pF

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **TYPICAL CHARACTERISTICS**

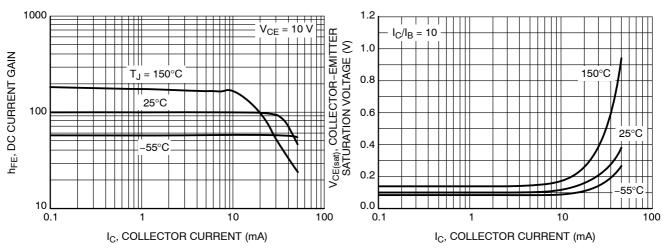


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

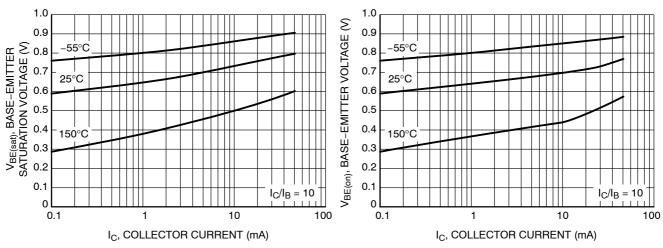


Figure 3. Base-Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base-Emitter On Voltage vs. Collector Current

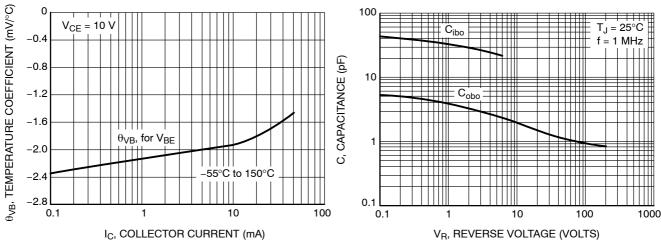


Figure 5. Base–Emitter Temperature Coefficient

Figure 6. Capacitance

#### **TYPICAL CHARACTERISTICS**

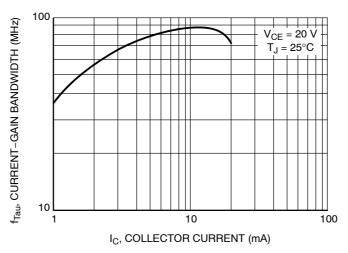


Figure 7. Current-Gain — Bandwidth Product

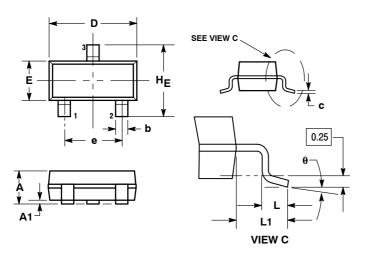
#### **ORDERING INFORMATION**

Device Order Number	Package Type	Shipping <sup>†</sup>		
MMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel		
SMMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel		
MMBTA42LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
SMMBTA42LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
MMBTA43LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

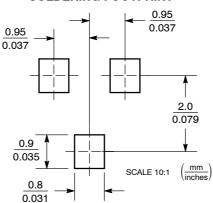
STYLE 6:

PIN 1. BASE

EMITTER 2.

COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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